



CBAT54W: SINGLE
CBAT54AW: DUAL, COMMON ANODE
CBAT54CW: DUAL, COMMON CATHODE
CBAT54SW: DUAL, IN SERIES

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	SYMBOL		UNITS
Continuous Reverse Voltage	V_R	30	V
Continuous Forward Current	I_F	200	mA
Peak Repetitive Forward Current	I_{FRM}	300	mA
Forward Surge Current, $t_p=10\text{ms}$	I_{FSM}	600	mA
Power Dissipation	P_D	250	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	Θ_{JA}	500	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MAX	UNITS
I_R	$V_R=25\text{V}$	2.0	μA
V_F	$I_F=0.1\text{mA}$	240	mV
V_F	$I_F=1.0\text{mA}$	320	mV
V_F	$I_F=10\text{mA}$	400	mV
V_F	$I_F=30\text{mA}$	500	mV
V_F	$I_F=100\text{mA}$	800	mV
C_d	$V_R=1.0\text{V}, f=1.0 \text{ MHz}$	10	pF
t_{rr}	$I_F=I_R=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$	5.0	ns

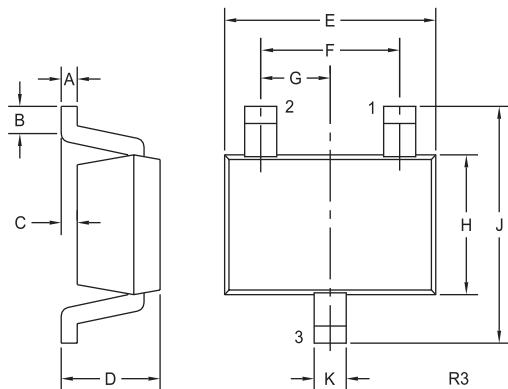
CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBAT54W Series types are Silicon Schottky Diodes in an SOT-323 Surface Mount Package.

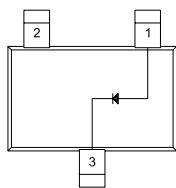
SURFACE MOUNT
SILICON SCHOTTKY DIODES

SOT-323 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.002	0.008	0.05	0.20
B	0.004	-	0.10	-
C	-	0.004	-	0.10
D	0.031	0.043	0.80	1.10
E	0.071	0.087	1.80	2.20
F	0.051		1.30	
G	0.026		0.65	
H	0.045	0.053	1.15	1.35
J	0.079	0.087	2.00	2.20
K	0.008	0.016	0.20	0.40

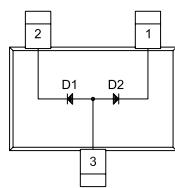
SOT-323 (REV: R3)



LEAD CODE:

- CBAT54W**
1) Anode
2) No Connection
3) Cathode

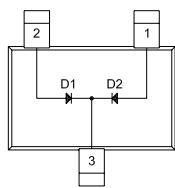
**MARKING
CODE: C4L**



LEAD CODE:

- CBAT54AW**
1) Cathode D2
2) Cathode D1
3) Anode D1, Anode D2

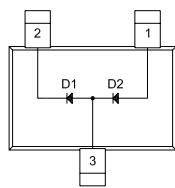
**MARKING
CODE: C42**



LEAD CODE:

- CBAT54CW**
1) Anode D2
2) Anode D1
3) Cathode D1, Cathode D2

**MARKING
CODE: C4C**



LEAD CODE:

- CBAT54SW**
1) Anode D2
2) Cathode D1
3) Anode D1, Cathode D2

**MARKING
CODE: C44**